



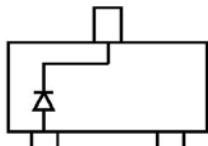
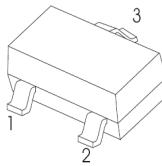
DONGGUAN NANJING ELECTRONICS LTD.,  
**SOT-23 Plastic-Encapsulate Diodes**

**BAS40/-04/-05/-06** SCHOTTKY BARRIER DIODE

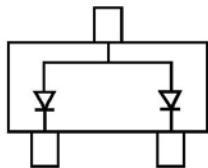
**FEATURES**

- Low Forward Voltage
- Fast Switching

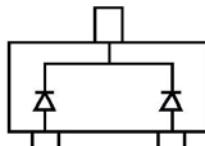
SOT-23



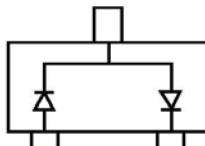
BAS40 MARKING: 43•



BAS40-06 MARKING: 46



BAS40-05 MARKING: 45



BAS40-04 MARKING: 44

**Maximum Ratings @Ta=25°C**

Parameter	Symbol	Limit	Unit
Peak repetitive peak reverse voltage	V <sub>RRM</sub>		
Working peak reverse voltage	V <sub>RWM</sub>	40	V
DC blocking voltage	V <sub>R</sub>		
Forward continuous current	I <sub>FM</sub>	200	mA
Power dissipation	P <sub>D</sub>	200	mW
Thermal resistance junction to ambient	R <sub>θJA</sub>	500	°C/W
Junction temperature	T <sub>J</sub>	125	°C
Storage temperature range	T <sub>STG</sub>	-55~+150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V <sub>(BR)</sub>	I <sub>R</sub> = 10µA	40		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =30V		200	nA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =1mA I <sub>F</sub> =40mA		380 1000	mV
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =0,f=1MHz		5	pF
Reverse recovery time	t <sub>rr</sub>	I <sub>rr</sub> =1mA, I <sub>R</sub> =I <sub>F</sub> =10mA R <sub>L</sub> =100Ω		5	ns

# Typical Characteristics

BAS40/-04/-05/-06

